

TO-92 Plastic-Encapsulate Transistors

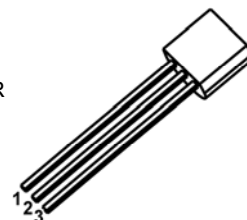
2SB562 TRANSISTOR (PNP)

FEATURES

- Low frequency power amplifier
- Complementary pair with 2SD468

TO-92

1. EMITTER
2. COLLECTOR
3. BASE



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Breakdown Voltage	-25	V
V _{CEO}	Collector-Emitter Breakdown Voltage	-20	V
V _{EBO}	Emitter-Base Breakdown Voltage	-5	V
I _C	Collector Current -Continuous	-1	A
P _C	Collector Dissipation	625	mW
R _{θJA}	Thermal Resistance from Junction to Ambient	200	°C/W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-10μA, I _E =0	-25			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-20			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-20V, I _E =0			-1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0			-1	μA
DC current gain	h _{FE}	V _{CE} =-2V, I _C =-0.5A	85		240	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-0.8A, I _B =-0.08A			-0.5	V
Base-emitter voltage	V _{BE}	V _{CE} =-2V, I _C =-0.5A			-1	V
Transition frequency	f _T	V _{CE} =-2V, I _C =-0.5A		350		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		38		pF

CLASSIFICATION OF h_{FE}

Rank	B	C
Range	85-170	120-240

